

# **MEMS Deformable Mirror Development for Space-Based Exoplanet Detection**



**Iris AO, Inc.**

**NASA Phase II SBIR: NNX11CE94P**

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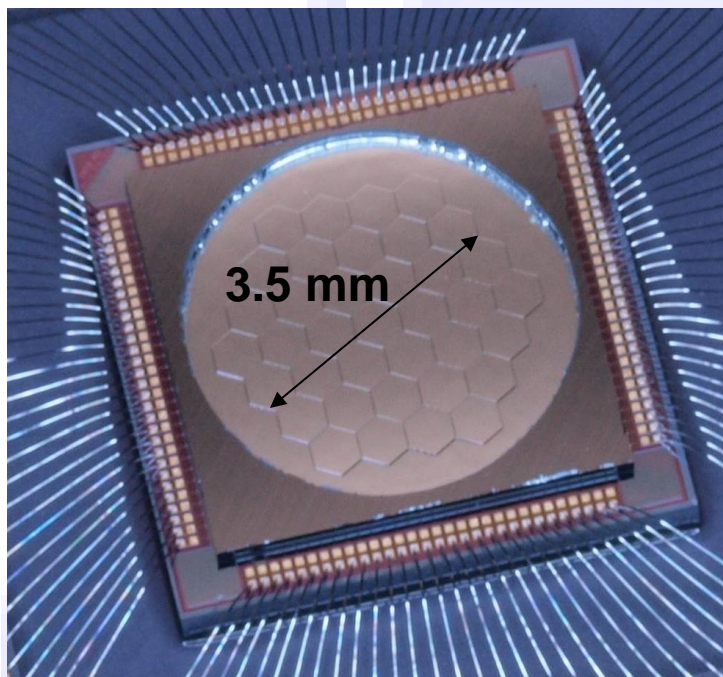
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# Iris AO Segmented DM Background

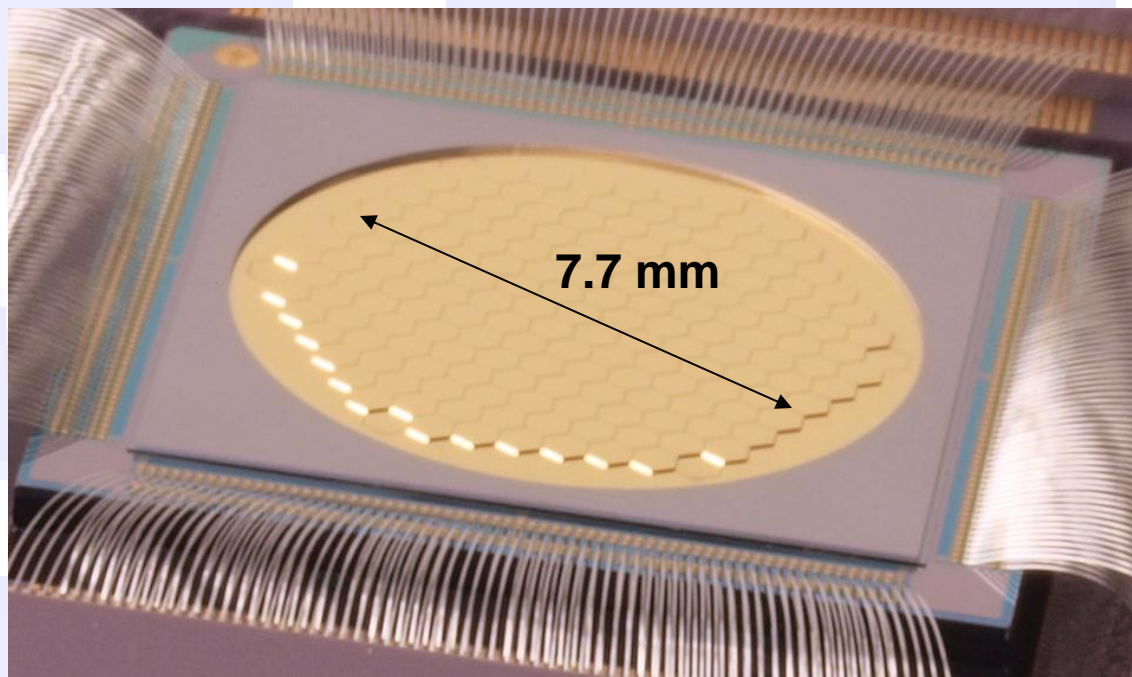


# Iris AO MEMS Segmented Deformable Mirrors



## **PTT111 DM**

- 111 Actuators
- 37 PTT Segments
- 3.5 mm inscribed aperture
- Factory calibrated

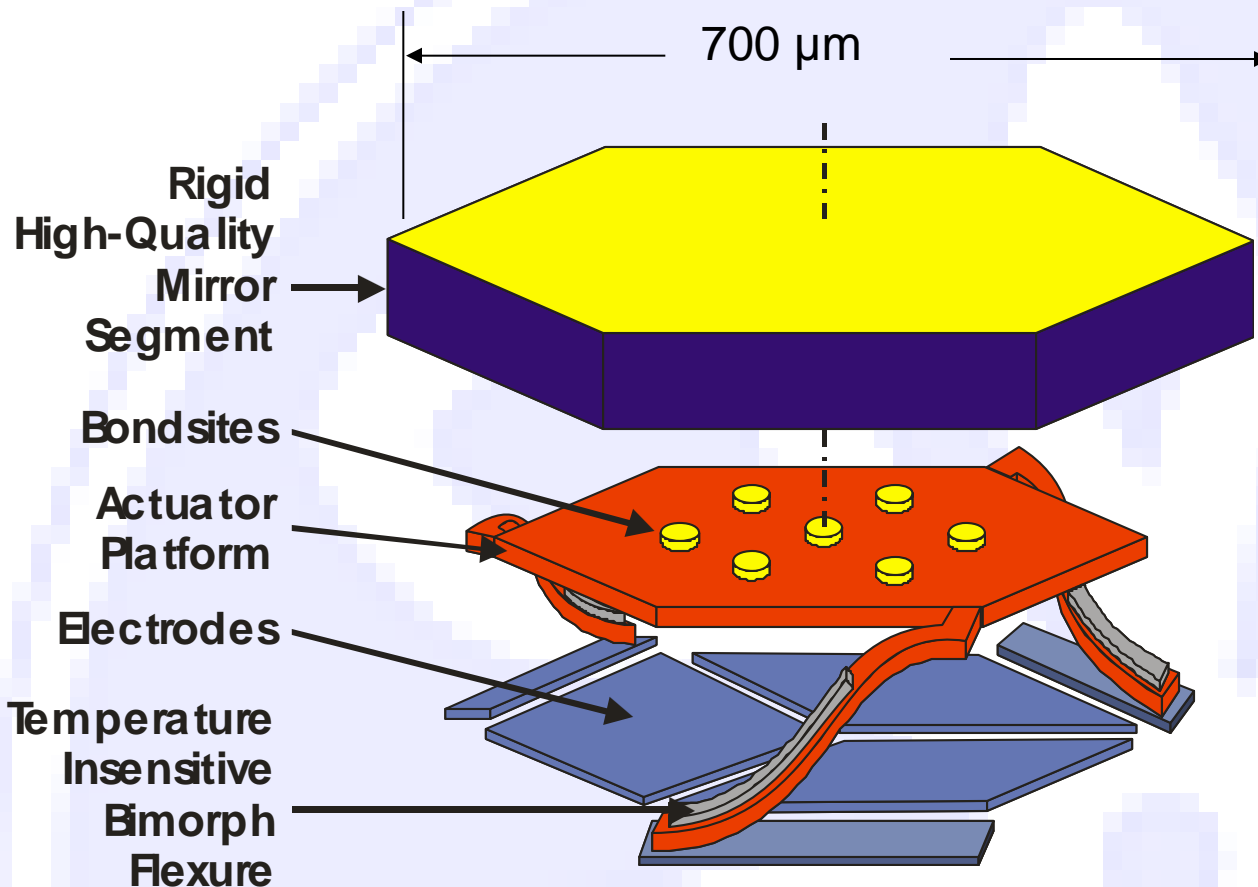


## **PTT489 DM**

- 489 Actuators
- 163 PTT Segments
- 7.7 mm inscribed aperture
- Factory calibrated



# Iris AO Segmented DM Background



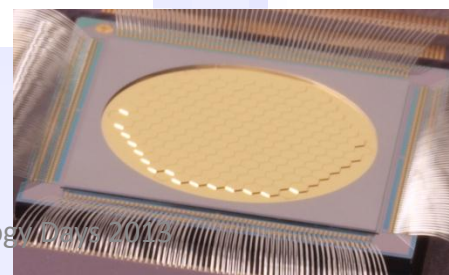
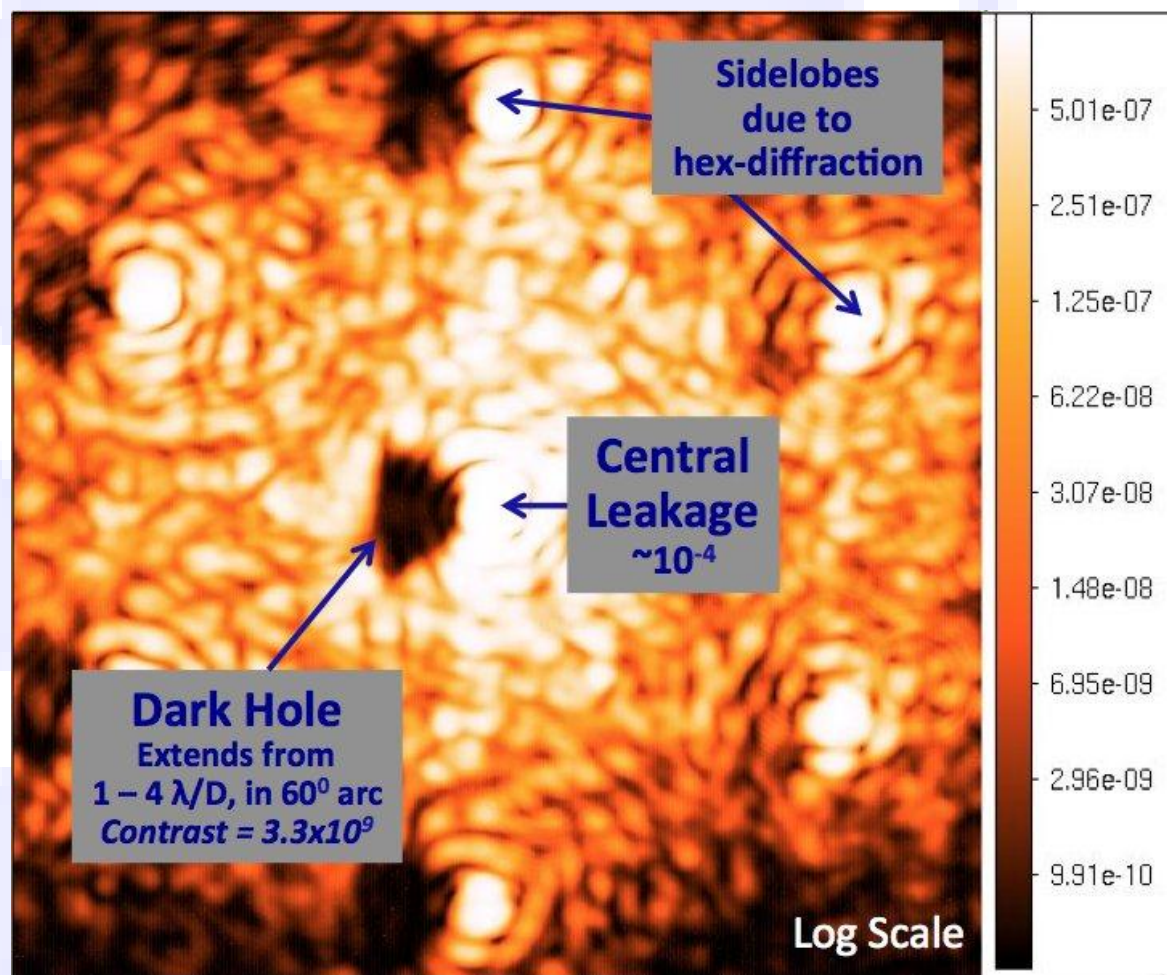
- 3 DOF: Piston/tip/tilt electrostatic actuation – no hysteresis
- Hybrid fabrication process
  - 3-poly surface micromachining
  - Single-crystal-silicon assembled mirror
- Unit cell easily tiled to create large arrays
- Hybrid technology
  - Thick mirror segments
  - Enables back-side stress-compensation coatings





# **$10^9$ Contrast @ IWA 1 – 4 $\lambda/D$ Results GSFC VNC Instrument on 06/09/12**

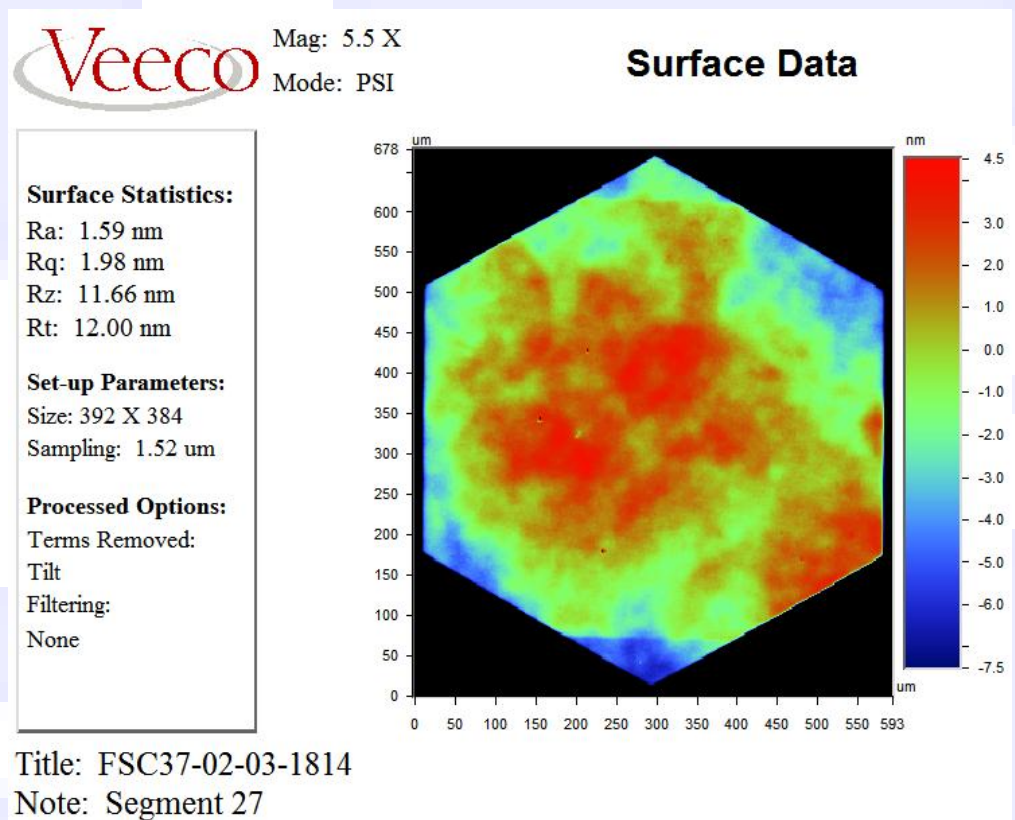
- GSFC/Visible Nulling Coronagraph
- 4 Data Collection Events (DCE)
  - 50,000 frames per DCE
  - Average last 3,800 frames
  - Closed-loop at 40 Hz / 4 Hz in vacuum tank
  - $(\lambda, \Delta\lambda) = (633, 1.2)$  nm
- **$>10^9$  Contrast averaged over 1-4  $\lambda/D$ , 60° arc region**
- 1<sup>st</sup> Demo of segmented aperture coronagraphy
  - hex-packed segmented MEMS DM
- Meets FY10/11 TDEM milestones
- FY12/13 TDEM broadband
  - increase spectral bandpass from  $\Delta\lambda = 1.2$  nm to  $\Delta\lambda = 40$  nm
- VNC investigated in 3 Astrophysics Strategic Mission Concept Studies
  - ATLAST, EPIC, DAVINCI





# Exoplanet Imaging Requirements: VNC Technology

- Usable Dynamic Range (Stroke): 0.5  $\mu\text{m}$
- Segment Control Resolution: 50  $\mu\text{m}$
- ~1000 Segment DM
- Segment Flatness: 1-3 nm *rms*
  - 2 nm *rms* demonstrated on best segment
- Robust to snap-in failures
  - Anti-snap-in device (ASD) technology survives 100M snap-in events



# Phase II Objectives

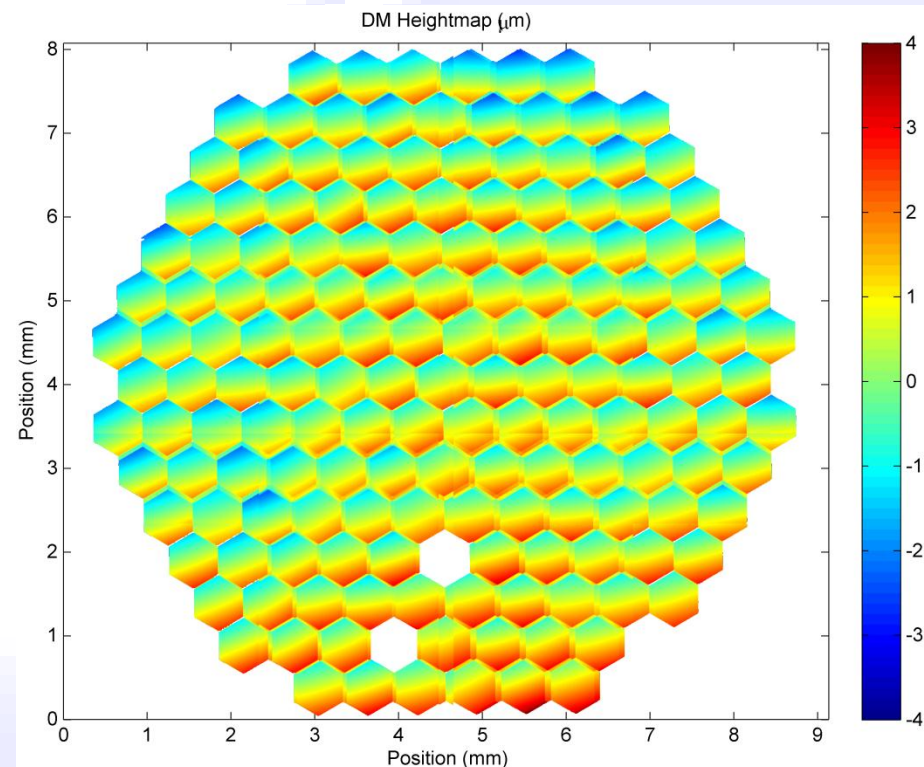
- Improve DM quality
  - Reduce chip bow
  - Increase segment position uniformity
  - Improve segment flatness for entire array
- Scale technology to 1000-actuator DM
  - Increase yield
  - Demonstrate PTT939 array
- Demonstrate pm-level positioning



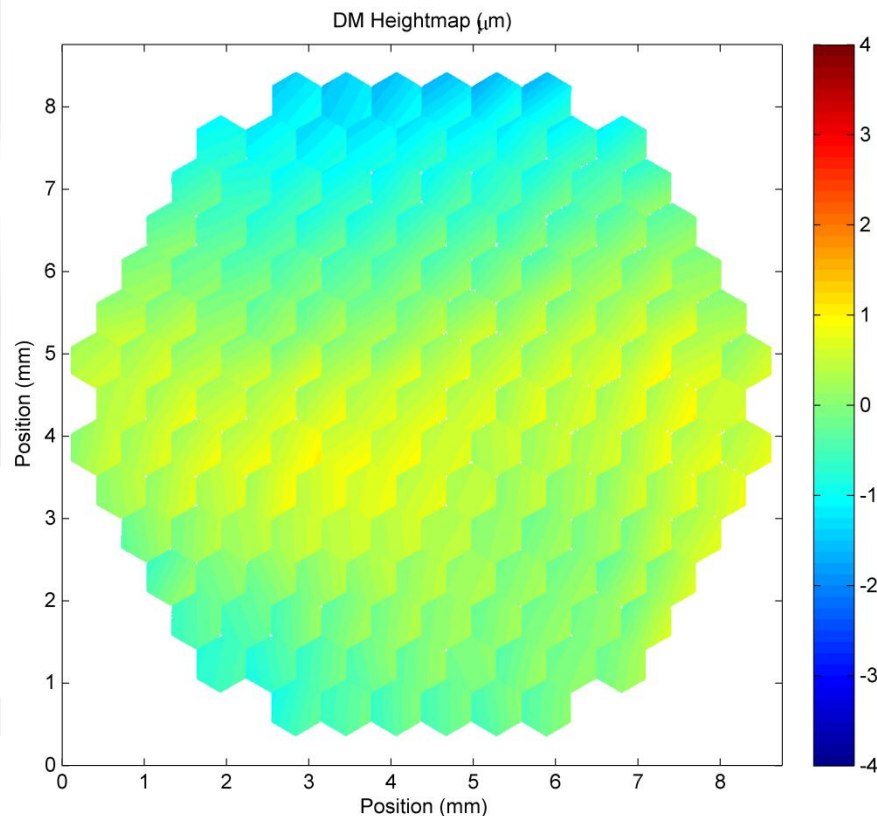


# NASA Phase II Result: DM Quality Improvement

## Unpowered PTT489 DM



**Pre Phase II**

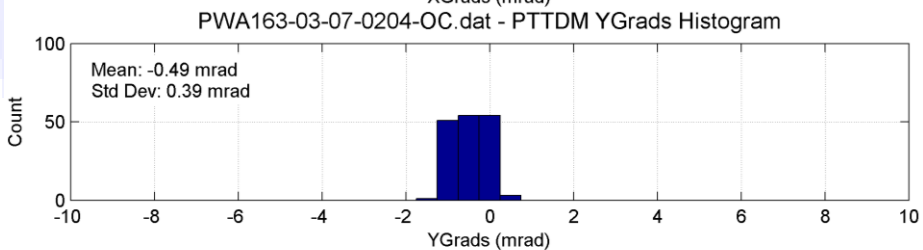
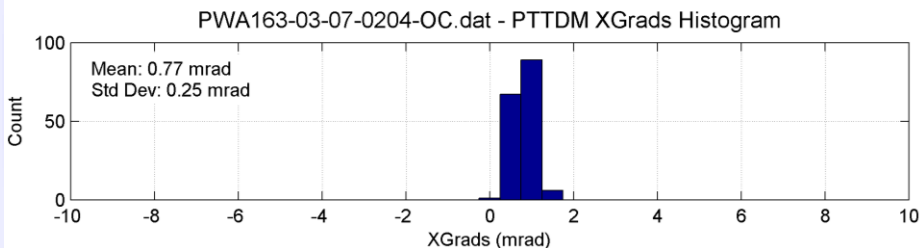
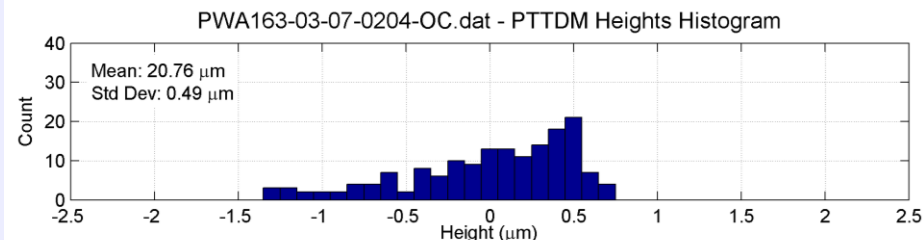
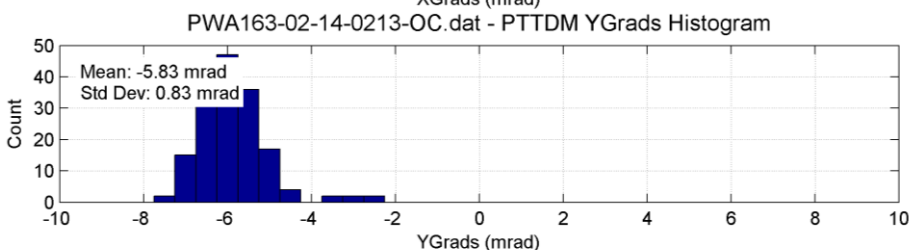
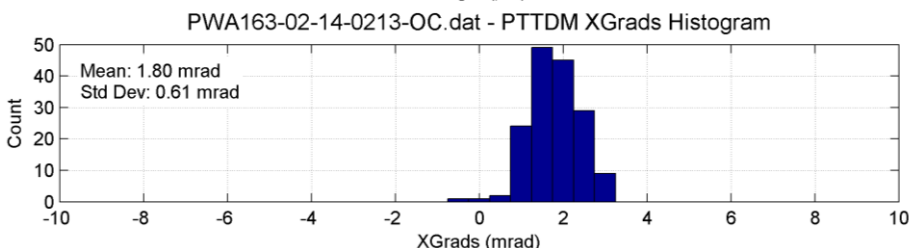
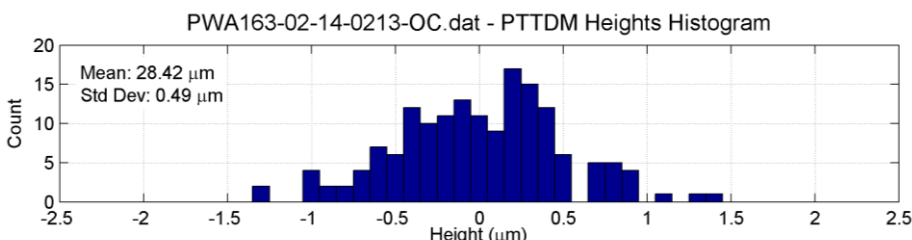


**Phase II Interim Deliverable**





# NASA Phase II Result: DM Quality Improvement



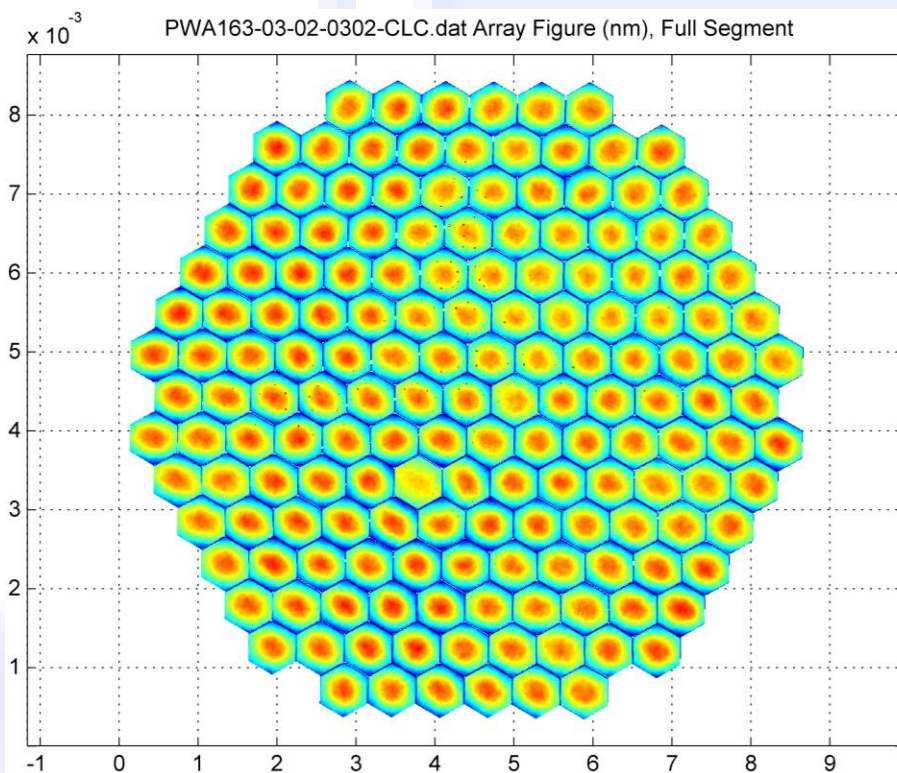
## Pre Phase II

## Phase II Interim Deliverable

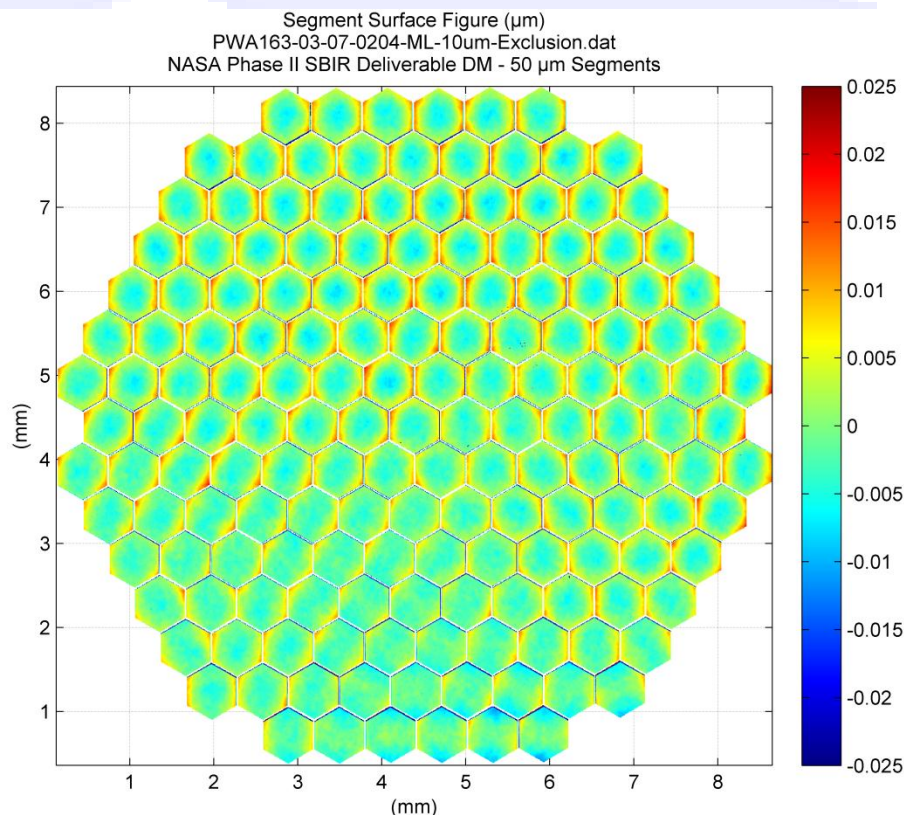
- Further improvements expected when fabrication technology transferred to DUV photolithography system



# NASA Phase II Result: DM Quality Improvement



**Pre Phase II**

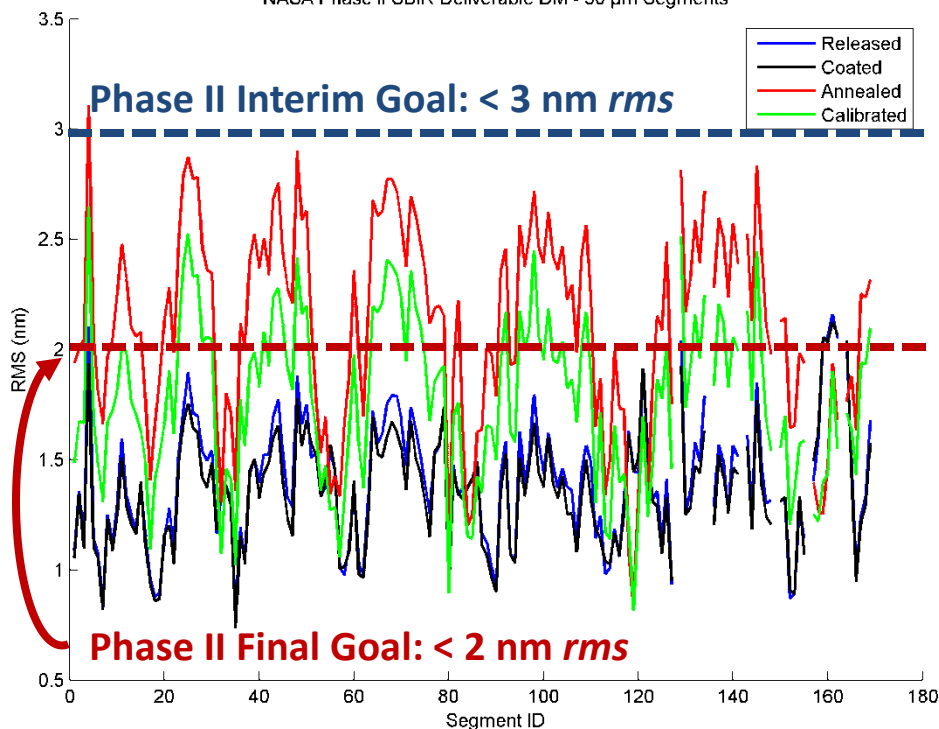


**Phase II Interim Deliverable**

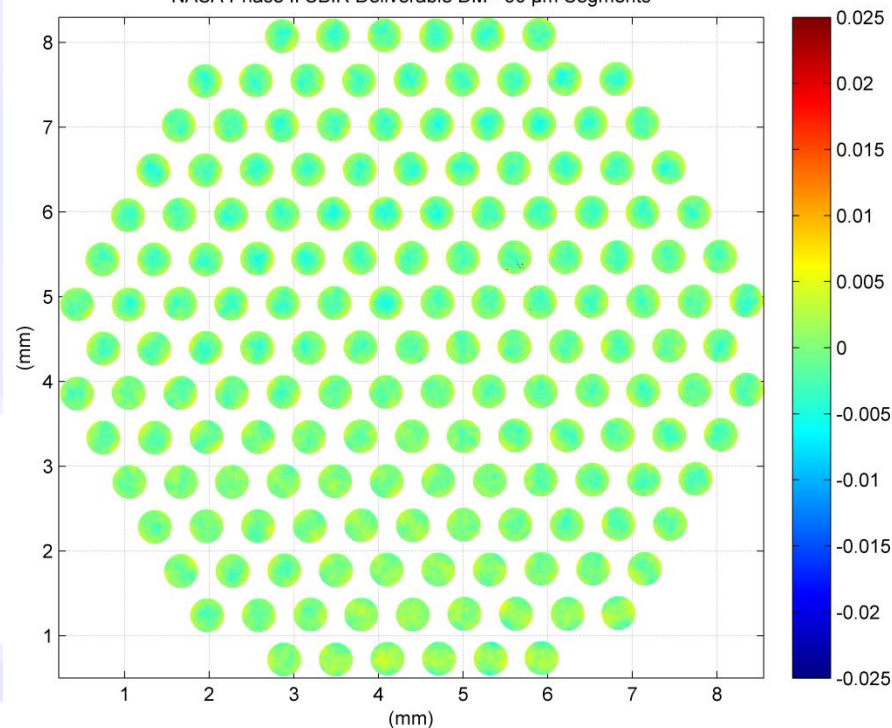


# NASA Phase II Result: DM Quality Improvement

RMS Segment Figure Errors (nm rms)  
PWA163-03-07-0204-REL-400um-Aperture.mat  
NASA Phase II SBIR Deliverable DM - 50  $\mu$ m Segments



Segment Surface Figure ( $\mu$ m)  
PWA163-03-07-0204-ML-400um-Aperture.dat  
NASA Phase II SBIR Deliverable DM - 50  $\mu$ m Segments

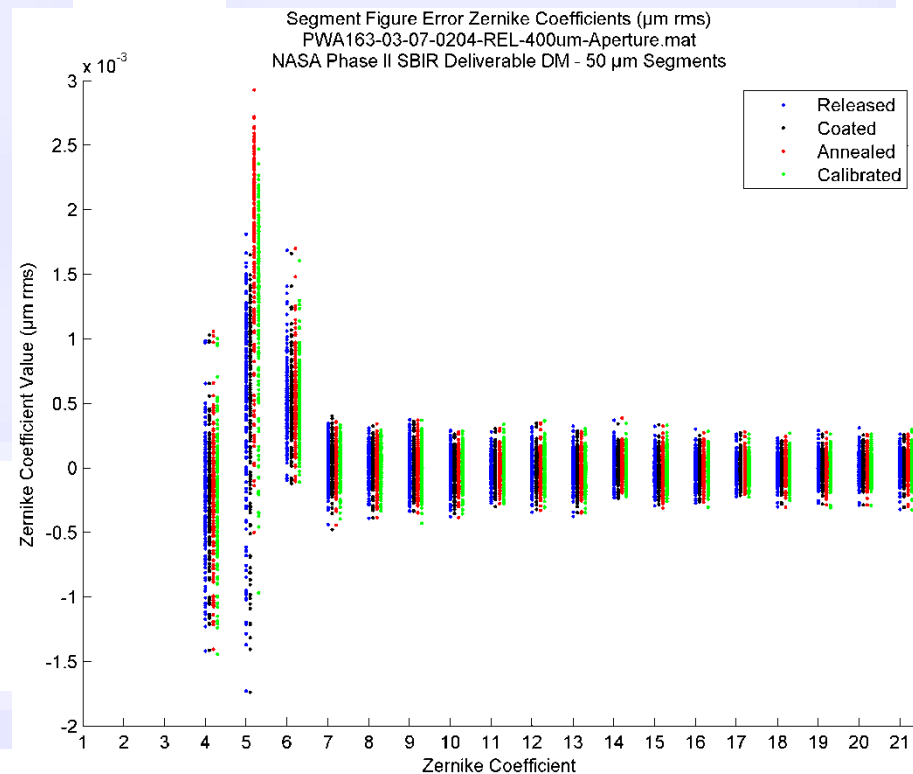


**Phase II Interim Deliverable**



# DM Segment Fitting – Zernike Coefficients

- Individual segments fit with Zernike terms
  - 400  $\mu\text{m}$  circular aperture
- Fitting errors dominated by low-order terms
- Starting silicon wafers are assumed flat
- DM fabrication processes introduce low-order deformations
- Room for improvements







# NASA Phase II Result: Yield Increases

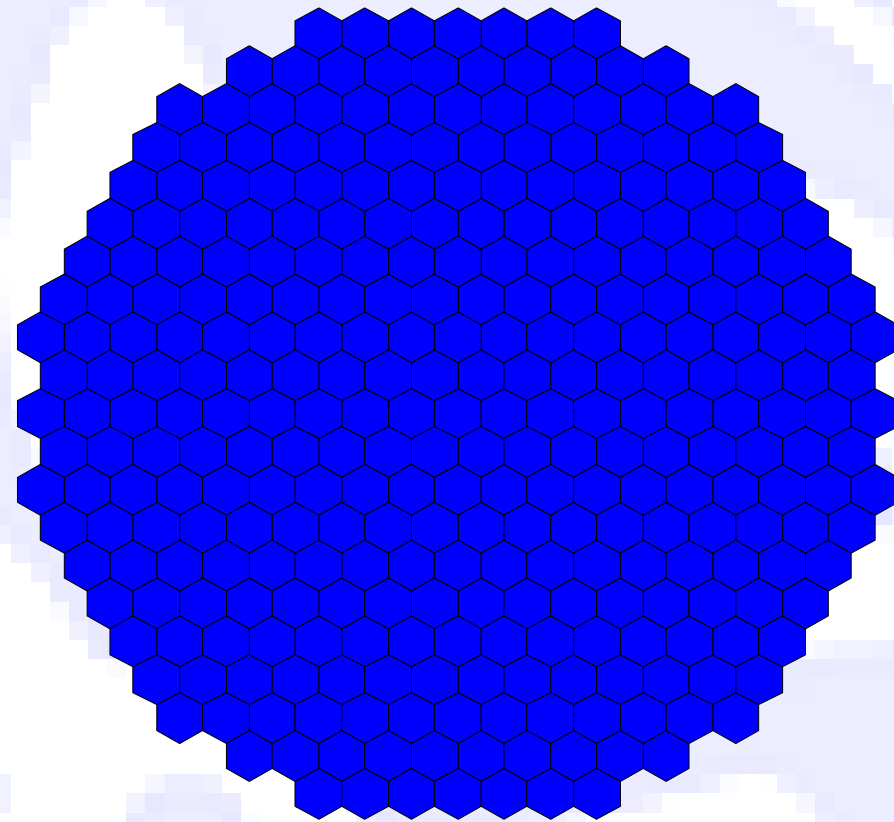
- Segment yield must be increased to demonstrate a fully functional PTT939 array
- Dominant electrical yield reduction identified
  - Low breakdown voltage of a passivation layer
  - Short-loop fabrication run nearly complete to test thicker passivation layer
- Dominant mechanical yield reduction identified
  - Gases generated during microstructure wet release process damage segments
  - Chemical treatments of DMs prior to release have improved yield
  - Design modification will be implemented to reduce chemical reactions

Mirror Build	Actuator Wafer Version	Mirror Wafer Version	Mech. Segment Yield	Electrical Segment Yield	Total Segment Yield	Chip Yield
1	1	1	66.8%	83.4%	55.7%	0.0%
2	1	2	93.9%	92.4%	86.8%	0.0%
3	2	2	97.6%	98.8%	96.8%	18.8%
4	2	2	98.8%	99.1%	96.5%	20.0%
5	2	2	TBD	TBD	TBD	TBD



# NASA Phase II SBIR: Remaining Work

- Demonstrate PTT939 DM
  - Transition fabrication process to DUV stepper lithography system
- Demonstrate pm-level positioning resolution
  - Signal processing technique to increase effective resolution demonstrated



**PTT939 DM**  
**10.85 mm aperture**  
**313 PTT segments**  
**939 actuators**